

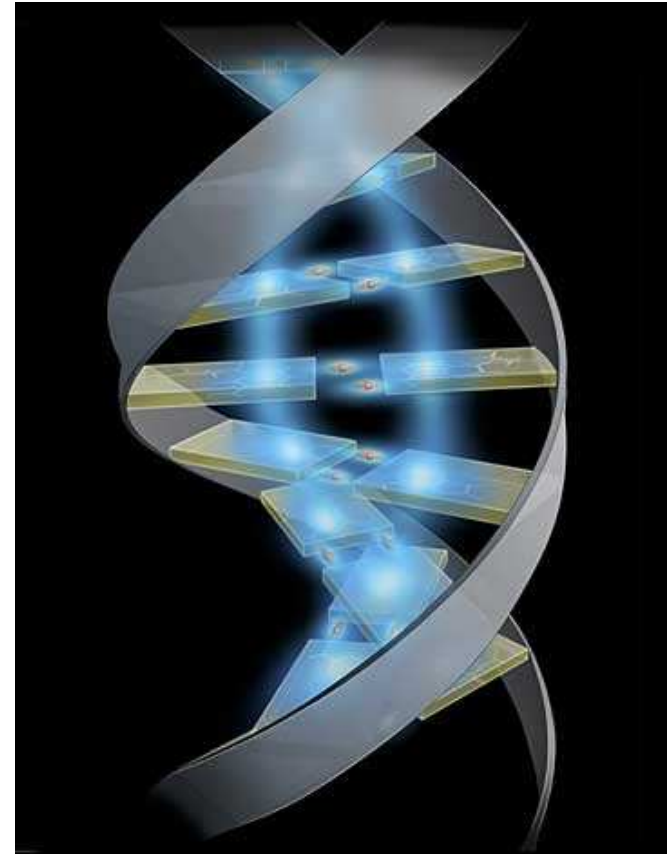
Quantum transport in DNA wires: Influence of a dissipative environment

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Molecular Computing Group

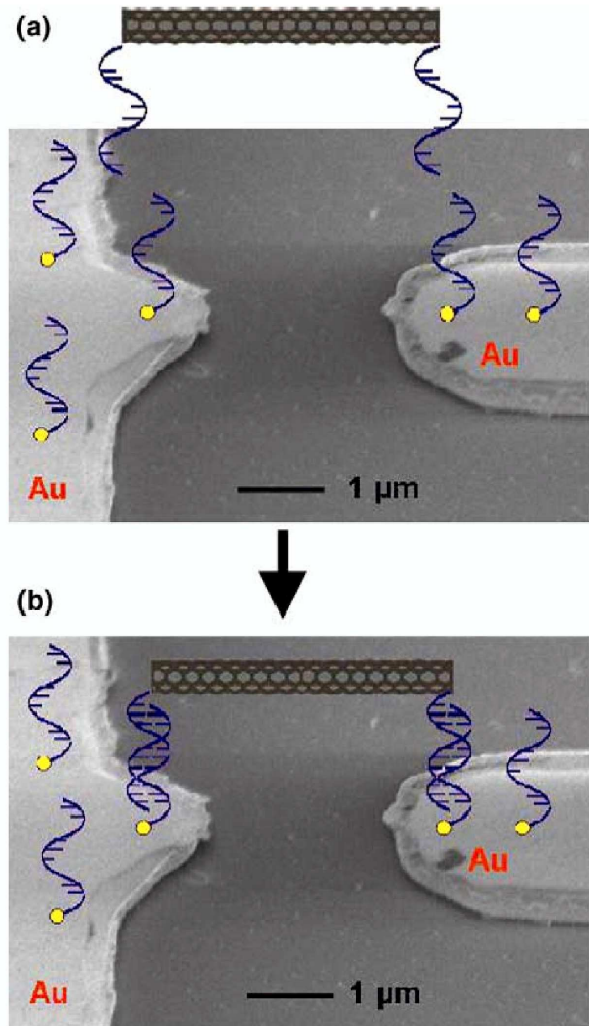
University of Regensburg



Outline

- Why DNA ?
- Electronic transport in DNA: a bird's eye view
- A model for a dissipative DNA wire
- Formalism and approximations
- Strong dissipative limit
- Conclusions

Why DNA ?



- **Groundbreaking** : repair of oxidative damage
 $\leadsto$ ET over long distances ($\sim 40 \text{ \AA}$)
(C. J. Murphy et al., Science (1993))
- Molecular electronics $\Rightarrow$ potential applications
as **template** (self-recognition and assembling)
as **molecular wire** (M-DNA, poly(GC))

Electronic transport in DNA: a bird's eye view

- **Experiments:** DNA is insulator, metal, semiconductor
 $\leadsto$ sample preparation and experimental conditions are crucial
 (dry vs. aqueous environment, metal-molecule contacts, single molecules vs. bundles . . .)
- **Theory:** Variety of factors modifying charge propagation:
 static disorder, dynamical disorder, environment (hydration shell, counterions)

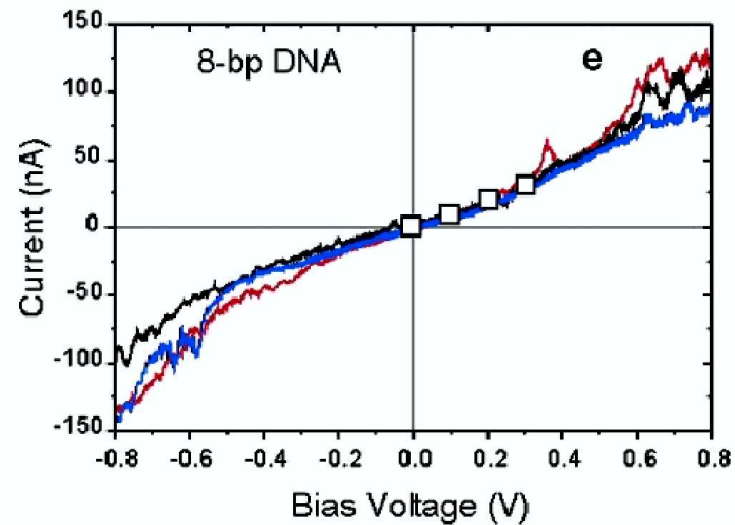
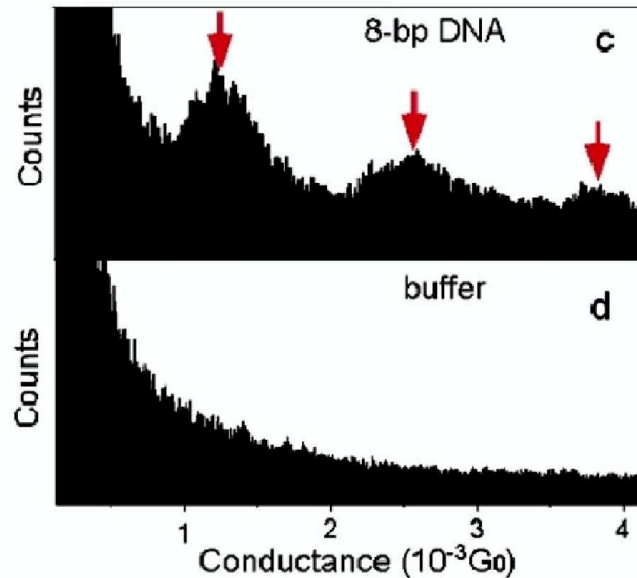
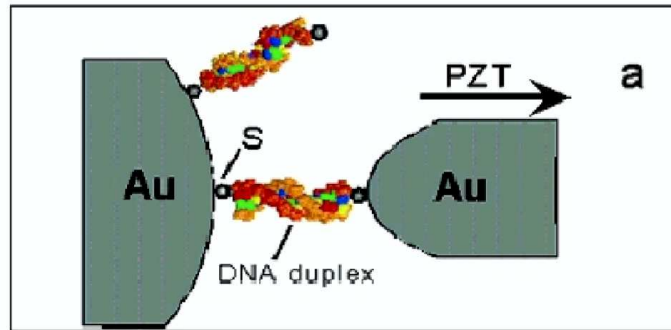
see: D. Porath, G. Cuniberti, and R. Di Felice,

Charge Transport in DNA-Based Devices

Top. Curr. Chem. (2004)

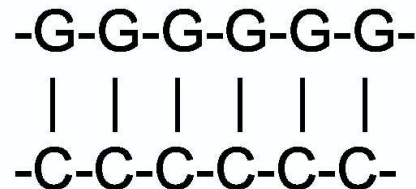
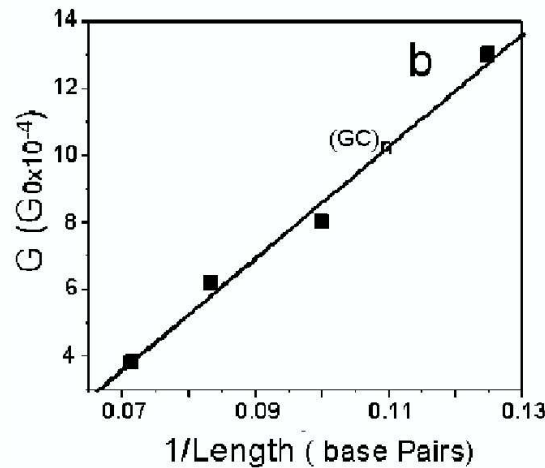
Transport in *single* Poly(GC) oligomers in *water*

B. Xu *et al.* Nanoletters 4, 1105 (2004)

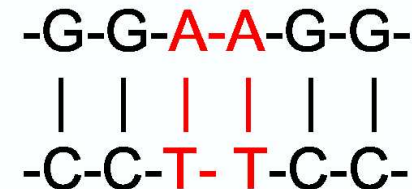
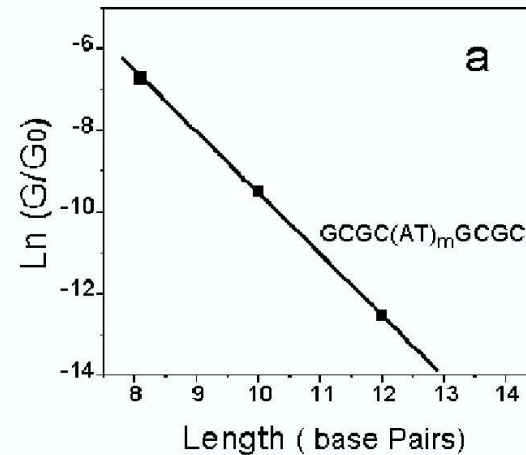


metallic behaviour

Transport in *single* Poly(GC) oligomers in *water*



$$g_{GC} \sim 1/L$$



$$g_{GC-AT} \sim e^{-\gamma L}$$

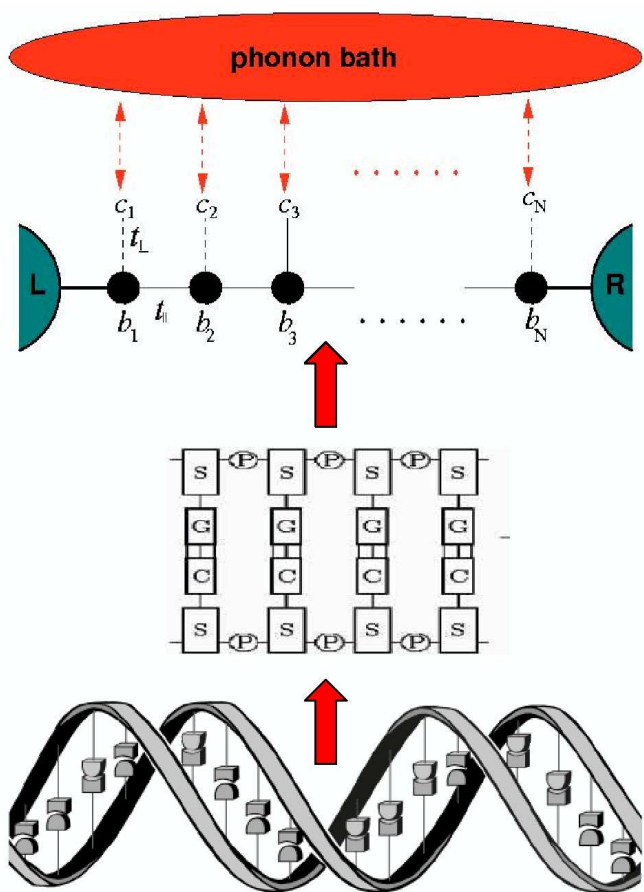
$$\gamma \sim 0.43 \text{ \AA}^{-1}$$

Ab initio (H. Wang *et al.* PRL (2004)): **dry** Poly(GC) $\rightsquigarrow e^{-\gamma L}$, $\gamma \sim 1.5 \text{ \AA}^{-1}$

Algebraic behaviour induced by the environment ?

A model for a dissipative DNA wire

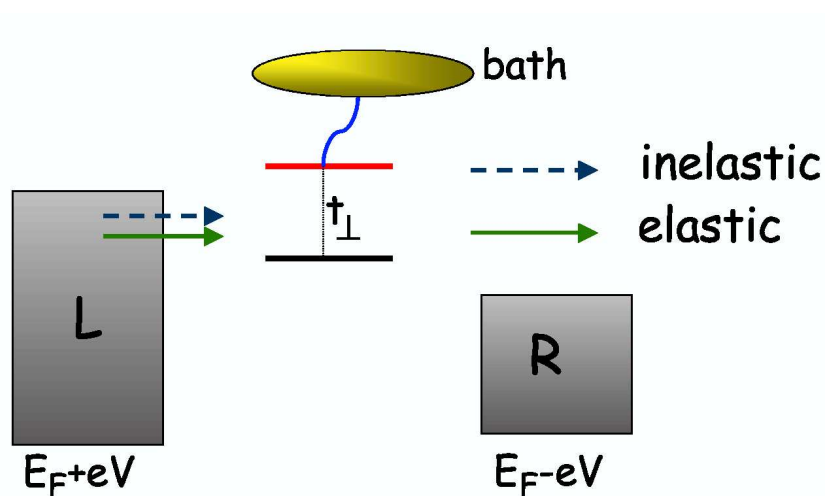
- *ab initio* $\leadsto$ (i) decoupled HOMO/LUMO channels, (ii) backbones non conducting, (iii) band gap ~ 2 eV (dry), but modified by water shell+counterions



$$\begin{aligned}
 \mathcal{H} = & \underbrace{\sum_j \epsilon_{b,j} b_j^\dagger b_j - t_{||} \sum_{\langle i,j \rangle} (b_i^\dagger b_j + \text{H.c.})}_{\mathcal{H}_c} + \underbrace{\sum_j \epsilon_j c_j^\dagger c_j}_{\mathcal{H}_c} \\
 & - \underbrace{t_{\perp} \sum_j (b_j^\dagger c_j + \text{H.c.})}_{\mathcal{H}_{c-c}} + \underbrace{\sum_{\mathbf{k} \in \text{L,R}, \sigma} \epsilon_{\mathbf{k}\sigma} d_{\mathbf{k}\sigma}^\dagger d_{\mathbf{k}\sigma}}_{\mathcal{H}_{\text{L/R}}} \\
 & + \underbrace{\sum_{\mathbf{k} \in \text{L}, \sigma} (V_{\mathbf{k},1} d_{\mathbf{k}\sigma}^\dagger b_1 + \text{H.c.}) + \sum_{\mathbf{k} \in \text{R}, \sigma} (V_{\mathbf{k},N} d_{\mathbf{k}\sigma}^\dagger b_N + \text{H.c.})}_{\mathcal{H}_{\text{L/R}-c}} \\
 & + \underbrace{\sum_{\alpha} \Omega_{\alpha} B_{\alpha}^\dagger B_{\alpha}}_{\mathcal{H}_B} + \underbrace{\sum_{\alpha,j} \lambda_{\alpha} c_j^\dagger c_j (B_{\alpha} + B_{\alpha}^\dagger)}_{\mathcal{H}_{\mathcal{F}-B}}.
 \end{aligned}$$

Formalism and approximations

- Green function techniques
- Phonon bath $\leadsto$ continuous frequency spectrum $J(\omega) \sim \left(\frac{\omega}{\omega_c}\right)^s$

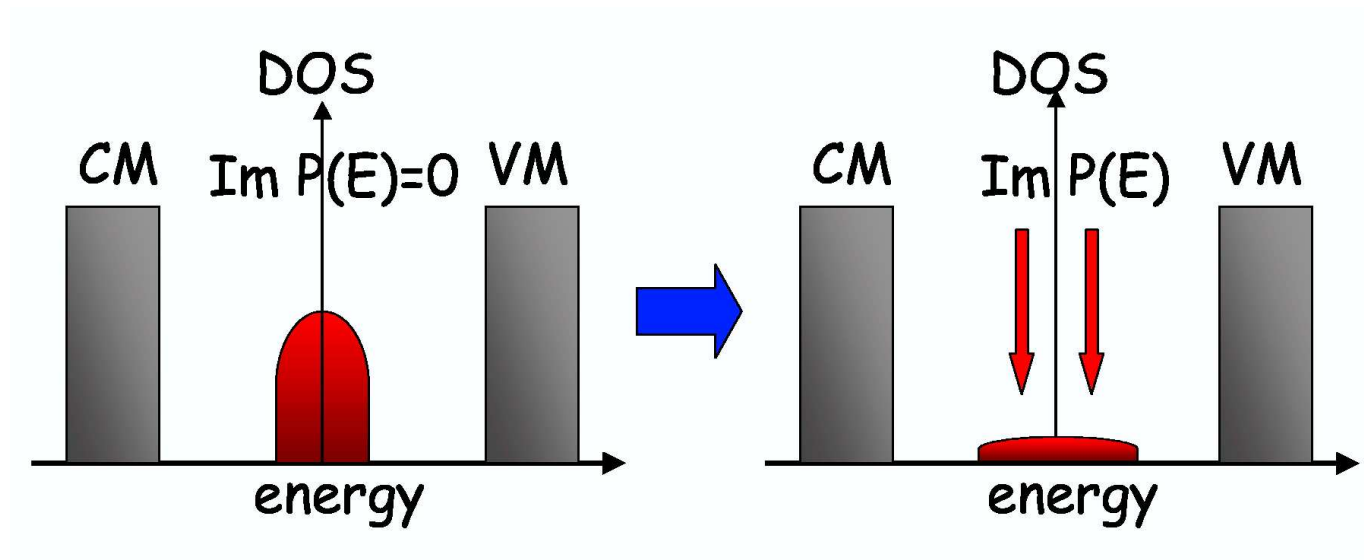


- Low-bias limit
 - $\leadsto$ neglect nonequilibrium effects
 - $\leadsto$ no **real** electron-phonon processes
- Landauer-like expression :
$$t(E) = \text{Tr}[G^\dagger \Gamma_R G \Gamma_L]$$

$t(E)$ includes **virtual** electron-phonon processes

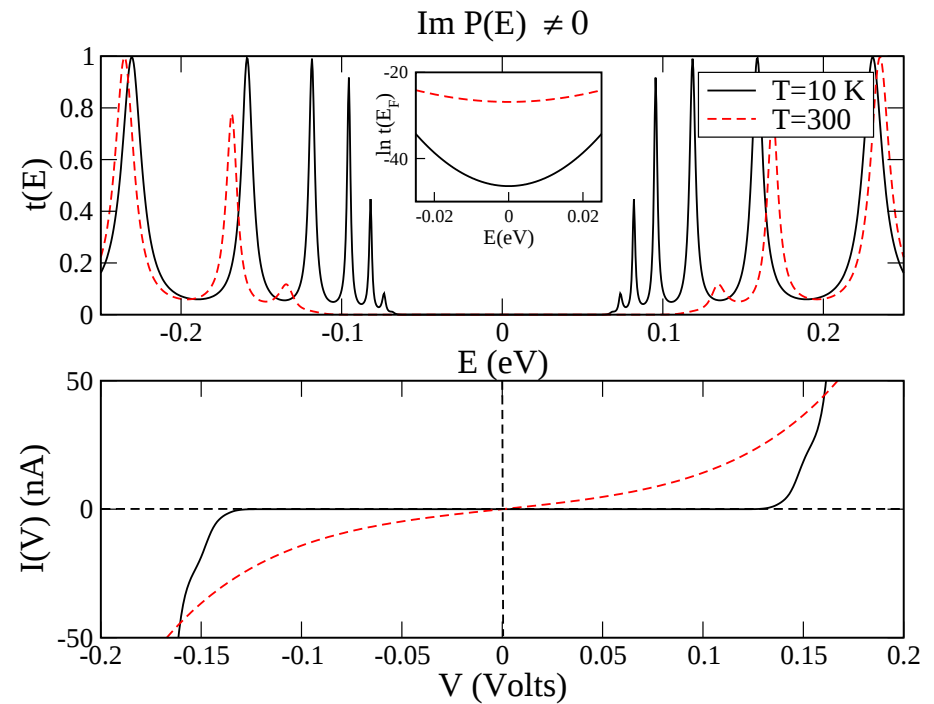
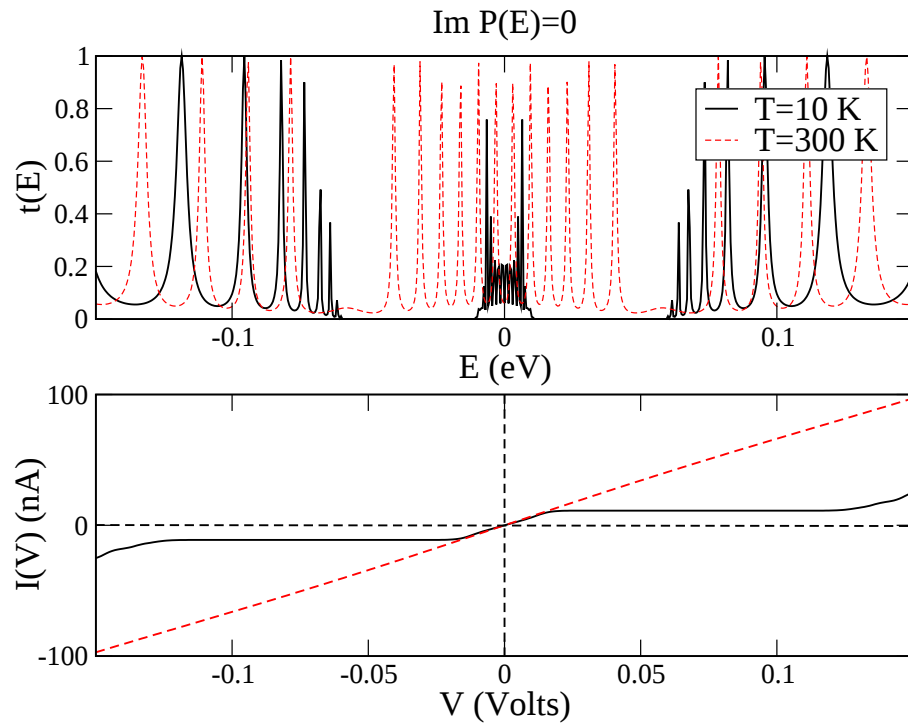
Low-bias, strong dissipative limit

New $k_B T$ -dependent electronic manifold around $E_F=0$



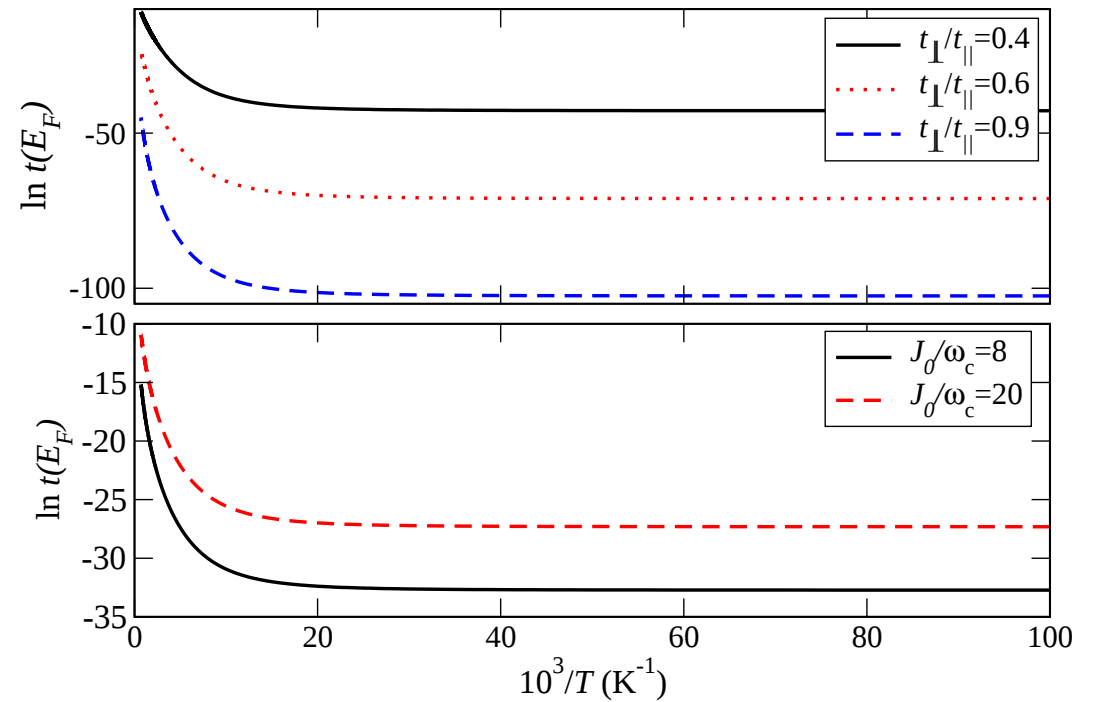
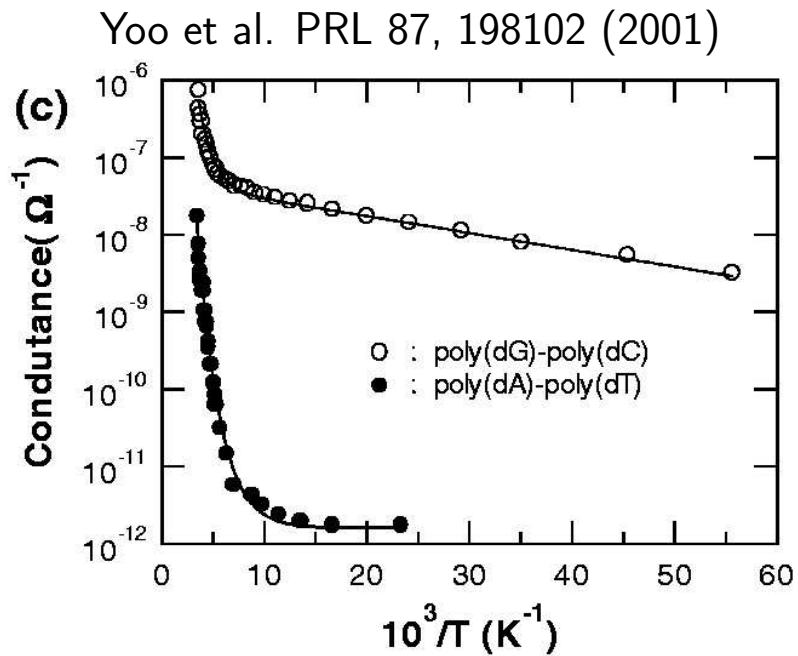
$\text{Im } P(E)$ (“bath-friction”) strongly suppresses the central manifold
incoherent polaronic band $\leadsto$ pseudo-gap opening

Transmission $t(E)$ and low-bias current $I(V)$



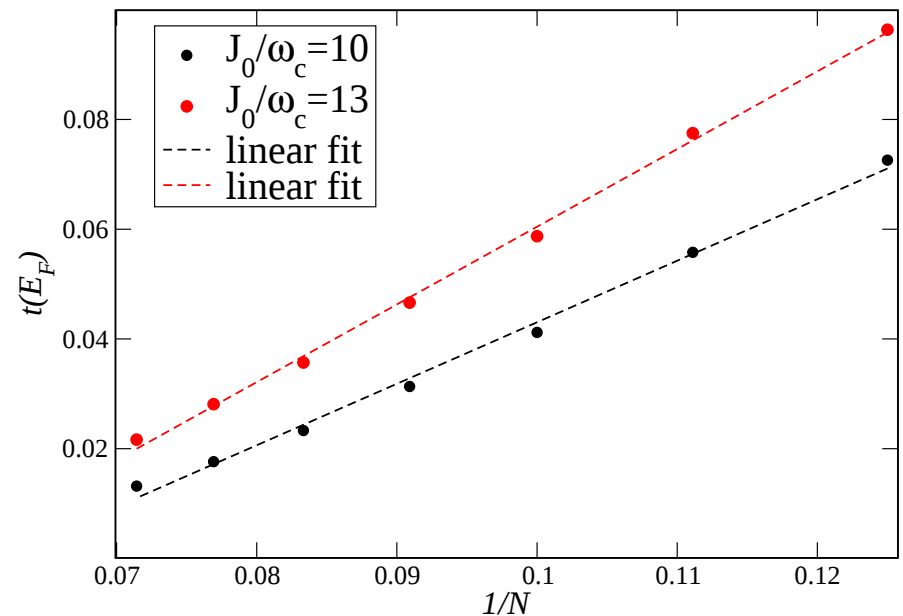
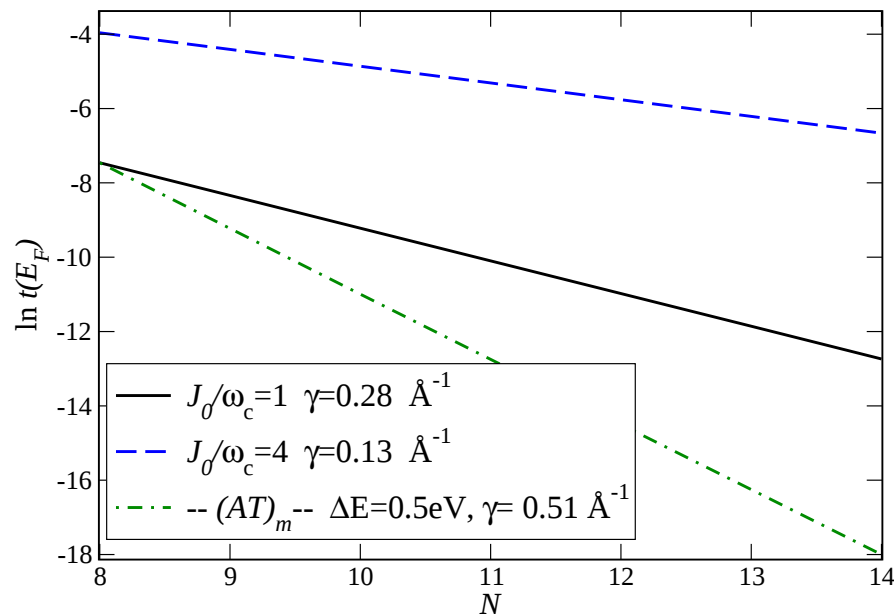
- pseudo-gap increases with temperature
- central band DOS also increases with temperature
- $I(V)$ displays “metallic” behaviour at high $k_B T$

Temperature dependence of $t(E_F)$ (Arrhenius plot)



Activated behaviour

Scaling of $t(E_F)$ with the chain length $L = Na_{\text{bp}}$



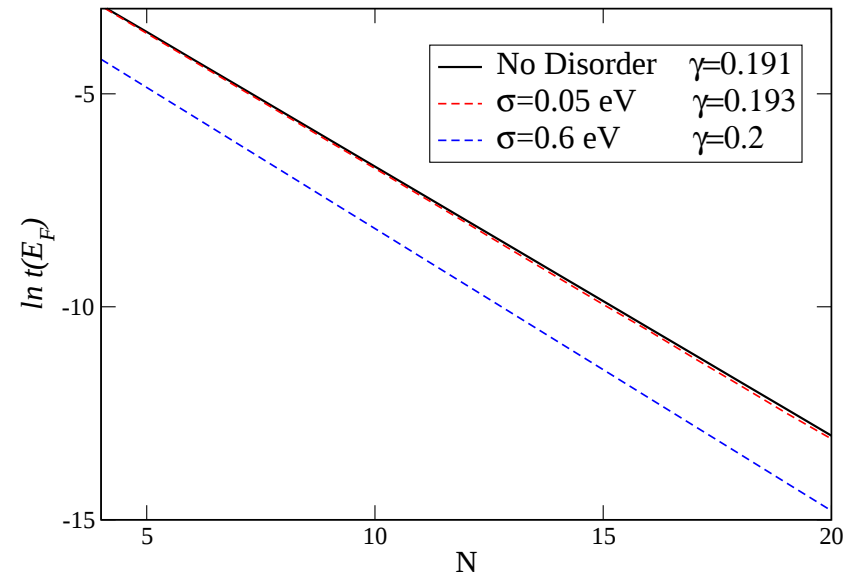
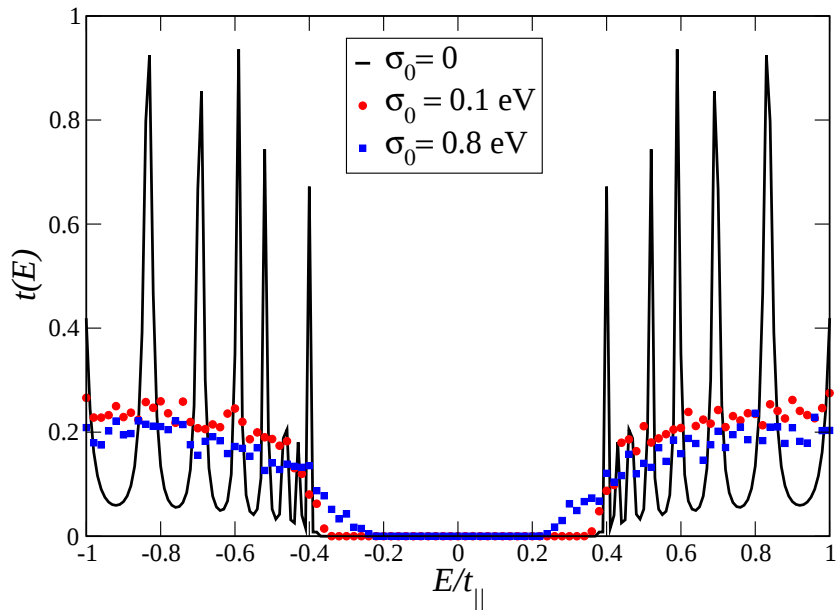
- Increasing coupling to the bath

exponential $t_F \sim e^{-\gamma L} \implies$ **algebraic** $t_F \sim L^{-\alpha}$ dependence

- Exponential dependence is not related to virtual tunneling through a gap ($\gamma \ll 1 \text{ \AA}^{-1}$)
- Introduction of a barrier $\rightsquigarrow (AT)_n$ pairs, enforces exp-dependence

Structural base-pairs fluctuations

Random on-site energies drawn from Gaussian distribution $P(\epsilon) = \frac{1}{\sqrt{2\pi}\sigma} e^{-\epsilon^2/2\sigma^2}$



Disorder does not appreciably affect the pseudo-gap formation

Conclusions

- Environment drastically affects charge transport
- Strong dissipative regime:
 - (i) bath-induced pseudo-gap
 - (ii) finite $k_B T$ -dependent DOS near $E_F \rightsquigarrow$ activated behaviourweak exponential or algebraic L -dependence
- Contact to Xue *et al.* experiments
 - (i) large currents $\sim 50 - 200 \text{ nA}$
 - (ii) (bath-induced) algebraic L -dependence
 - (iii) $\gamma[(AT)_n] \approx 0.15 \text{ \AA}^{-1} < \gamma^{\text{Xue}}[(AT)_n] = 0.43 \text{ \AA}^{-1}$

Perspectives

